

Title (en)  
Crystalline multilayer structure and semiconductor device

Title (de)  
Kristalline mehrschichtige Struktur und Halbleiterbauelement

Title (fr)  
Structure multi-couche cristalline et dispositif semi-conducteur

Publication  
**EP 2933825 B1 20170705 (EN)**

Application  
**EP 14199093 A 20141219**

Priority  
JP 2014072780 A 20140331

Abstract (en)  
[origin: EP2933825A1] Provided is a crystalline multilayer structure having good semiconductor properties. The crystalline multilayer structure includes a base substrate and a corundum-structured crystalline oxide semiconductor thin film disposed directly on the base substrate or with another layer therebetween. The crystalline oxide semiconductor thin film is 0.1  $\mu\text{m}$  or less in a surface roughness (Ra).

IPC 8 full level  
**H01L 29/786** (2006.01); **H01L 21/02** (2006.01); **H01L 29/66** (2006.01)

CPC (source: CN EP US)  
**H01L 21/0242** (2013.01 - CN EP US); **H01L 21/0243** (2013.01 - EP US); **H01L 21/02433** (2013.01 - CN); **H01L 21/02488** (2013.01 - EP US); **H01L 21/02565** (2013.01 - CN EP US); **H01L 21/0257** (2013.01 - CN); **H01L 21/02576** (2013.01 - EP US); **H01L 21/02581** (2013.01 - EP US); **H01L 21/02587** (2013.01 - EP US); **H01L 21/02598** (2013.01 - CN); **H01L 21/0262** (2013.01 - CN EP US); **H01L 21/02628** (2013.01 - EP US); **H01L 29/04** (2013.01 - CN); **H01L 29/06** (2013.01 - CN); **H01L 29/1033** (2013.01 - CN); **H01L 29/24** (2013.01 - CN US); **H01L 29/66969** (2013.01 - CN EP US); **H01L 29/78** (2013.01 - CN); **H01L 29/7869** (2013.01 - EP US); **H01L 29/78696** (2013.01 - EP US); **H01L 21/02631** (2013.01 - EP US)

Designated contracting state (EPC)  
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)  
**EP 2933825 A1 20151021; EP 2933825 B1 20170705**; CN 104952927 A 20150930; CN 104952927 B 20190813; CN 110176493 A 20190827; CN 110299414 A 20191001; CN 110310996 A 20191008; CN 110310996 B 20200908; JP 2015199649 A 20151112; JP 2018203614 A 20181227; JP 6379369 B2 20180829; JP 6539921 B2 20190710; TW 201536945 A 20151001; TW 201713790 A 20170416; TW 201829824 A 20180816; TW I571525 B 20170221; TW I625413 B 20180601; TW I665327 B 20190711; US 10090388 B2 20181002; US 11038026 B2 20210615; US 2015279944 A1 20151001; US 2019013384 A1 20190110

DOCDB simple family (application)  
**EP 14199093 A 20141219**; CN 201510145934 A 20150330; CN 201910497081 A 20150330; CN 201910634324 A 20150330; CN 201910634597 A 20150330; JP 2015070469 A 20150330; JP 2018126539 A 20180703; TW 104110315 A 20150330; TW 105143387 A 20150330; TW 107112140 A 20150330; US 201414578017 A 20141219; US 201816118402 A 20180830